

isc Silicon NPN Power Transistor

2SD1497

DESCRIPTION

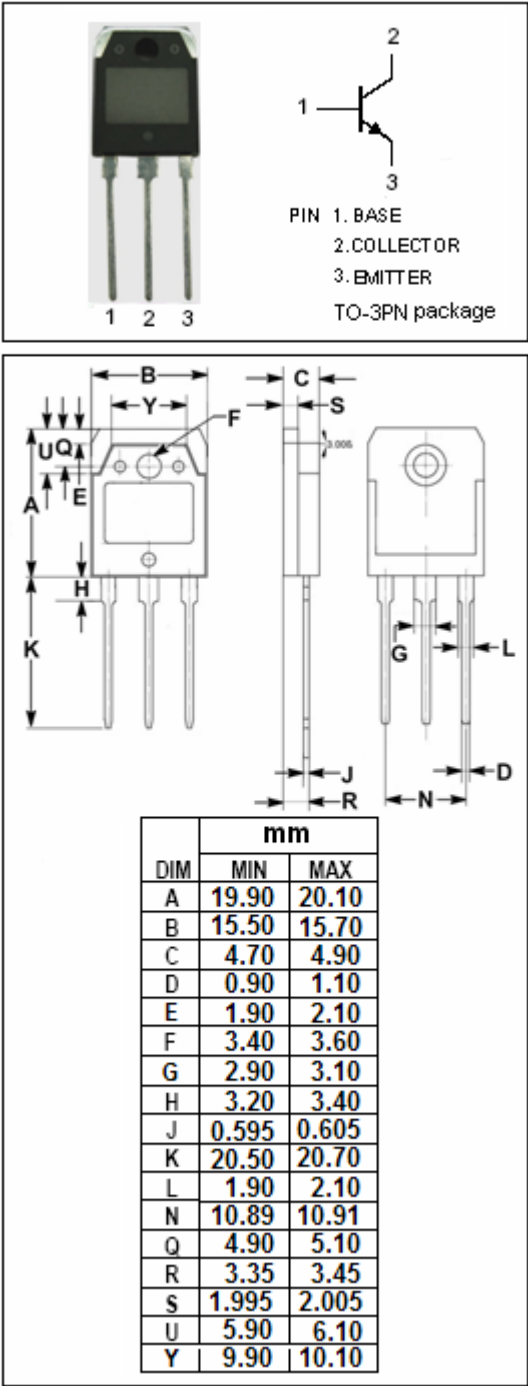
- High Breakdown Voltage-
: V_{CBO} = 1500V (Min)
- High Switching Speed

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	6	A
$I_{C(surge)}$	Collector Current-Surge	16	A
P_C	Collector Power Dissipation @ $T_C = 25^{\circ}\text{C}$	50	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-45~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**2SD1497****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; R _{BE} = ∞	600			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			1.5	V
I _{CEX}	Collector Cutoff Current	V _{CB} = 1500V; V _{EB} = 2V			1.0	mA
t _f	Fall Time	I _{CP} = 4A, I _{B1} = 1.3A			2.0	μs